

# DM74ALS13 Dual 4-Input NAND Gate with Schmitt Trigger Inputs

# **General Description**

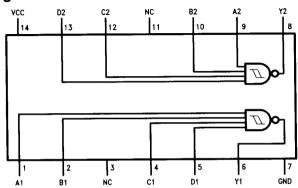
This device contains two independent gates, each of which performs the logic NAND function. Each input has hysteresis which increases the noise immunity and transforms a slowly changing input signal to a fast changing, jitter-free output.

### **Features**

- Input Hysteresis
- Low output noise generation

- High input noise immunity
- Switching specification at 50 pF
- Switching specifications guaranteed over full temperature and Voc range
- Advanced oxide-isolated, ion-implanted Schottky TTL process
- Functionally and pin-for-pin compatible with Schottky and Low Power Schottky TTL counterparts
- Improved AC performance over low power Schottky counterpart

# **Connection Diagram**



Order Number DM74ALS13M or DM74ALS13N See NS Package Number M14A or N14A

## **Function Table**

### $Y = \overline{ABCD}$

	Inputs				
A	В	С	D	Y	
X	Х	X	L	н	
х	×	L	Х	Н	
X	L	Х	Х	H	
L	X	Х	X	Н	
н	Н	н	н	L	

H = High Logic Level

L = Low Logic Level

X = Either Low or High Logic Level

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TL/F/8772

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TL/F/8772-1

# **Absolute Maximum Ratings**

 Supply Voltage
 7V

 Input Voltage
 7V

 Storage Temperature Range
 -65°C to +150°C

Operating Free Air Temperature Range

DM74ALS 0°C to +70°C Typical θ<sub>1</sub>Δ

N Package M Package

78.5°C/W 109.0°C/W Note: The "Absolute Maximum Ratings" are those values beyond which the safety of the device can not be guaranteed. The device should not be operated at these limits. The parametric values defined in the "Electrical Characteristics" table are not guaranteed at the absolute maximum ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.

# **Recommended Operating Conditions**

Symbol	Parameter			Units		
			Min	Nom	Max	Units
V <sub>CC</sub>	Supply Voltage		4.5	5	5.5	V
V <sub>T+</sub>	Positive-Going Input Threshold Voltage	V <sub>CC</sub> = Min to Max	1.4		2	V
		$V_{CC} = 5V$	1.55		1.85	] "
V <sub>T</sub> =	Negative-Going Input Threshold Voltage	V <sub>CC</sub> = Min to Max	0.75		1.2	V
		$V_{CC} = 5V$	0.85		1.1	
HYS	Input Hysteresis	V <sub>CC</sub> = Min to Max	0.5			V
		$V_{CC} = 5V$	0.6			]
I <sub>ОН</sub>	High Level Output Current				-0.4	mA
loL	Low Level Output Current				8	mA
$T_A$	Operating Free Air Temperature Range		0		70	°C

# Electrical Characteristics over recommended free air temperature range (unless otherwise noted)

Symbol	Parameter	Test Conditions		Min	Тур	Max	Units
V <sub>K</sub>	Input Clamp Voltage	$V_{CC} = Min, I_{I} = -18 \text{ mA}$				- 1.5	V
V <sub>OH</sub>	High Level Output Voltage	V <sub>CC</sub> = 4.5V to 5.5V, I <sub>OH</sub> = Max		V <sub>CC</sub> -2			V
V <sub>OL</sub>	Low Level Output Voltage	V <sub>CC</sub> = Min	I <sub>OL</sub> = 4 mA		0.25	0.4	V
			I <sub>OL</sub> = 8 mA		0.35	0.5	\ \ \
I <sub>T+</sub>	Input Current at Positive-Going Threshold Voltage	$V_{CC} = 5V$ , $V_I = V_{T+}$				20	μА
I <sub>T</sub> _	Input Current at Negative-Going Threshold Voltage	$V_{CC} = 5V$ , $V_I = V_{T-}$				- 100	μΑ
I <sub>I</sub>	Input Current at Maximum Input Voltage	$V_{CC} = Max, V_1 = 7V$				100	μА
I <sub>IH</sub>	High Level Input Current	$V_{CC} = Max, V_1 = 2.7V$				20	μА
I <sub>IL</sub>	Low Level Input Current	$V_{CC} = Max, V_1 = 0.4V$				- 100	μА
lo	Output Drive Current	$V_{CC} = Max, V_O = 2.25V$		-30		-112	mA
Іссн	Supply Current with Outputs High	V <sub>CC</sub> = Max				4	mA
ICCL	Supply Current with Outputs Low	V <sub>CC</sub> = Max				4	mA
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	V <sub>CC</sub> = 5.0V, T <sub>A</sub> = 25°C ( <i>Figures 1, 2</i> ; Notes 1, 2)			0.23		V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	V <sub>CC</sub> = 5.0V, T <sub>A</sub> = 25°C ( <i>Figures 1, 2</i> ; Notes 1, 2)			-0.2		V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage	V <sub>CC</sub> = 5.0V, T <sub>A</sub> = 25°C (Notes 1, 3)			1.64		v
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage	V <sub>CC</sub> = 5.0V, T <sub>A</sub> = 25°C (Notes 1, 3)			1.24		٧

Note 1: Plastic DIP package.

Note 2: n = number of device outputs, n - 1 outputs switching, each driven 0V to 3V one output @ GND.

Note 3: n = number of device outputs, n outputs switching, n - 1 outputs switching 0V to 3V. Input under test switching 3V to threshold (V<sub>ILD</sub>); 0V to threshold (V<sub>IHD</sub>); f = 1 MHz.

### Switching Characteristics over recommended operating free air temperature range

Symbol	Parameter	Conditions (Note 1)	DM74ALS13		Units
		Conditions (Note 1)	Min	Max	Office
t <sub>PLH</sub>	Propagation Delay Time Low to High Level Output	$V_{CC} = 4.5V \text{ to } 5.5V$ RL = 500 $\Omega$ , CL = 50 pF	2	12	
t <sub>PHL</sub>	Propagation Delay Time High to Low Level Output		2	12	ns ns

Note 1: See Section 1 for test waveforms and output load.

### **ALS Noise Characteristics**

The setup of a noise characteristics measurement is critical to the accuracy and repeatability of the tests. The following is a brief description of the setup used to measure the noise characteristics of ALS.

#### Equipment:

Word Generator
Printed Circuit Board Test Fixture
Dual Trace Oscilloscope

### Procedure:

- 1. Verify Test Fixture Loading: Standard Load 50 pF, 500Ω.
- 2. Deskew the word generator so that no two channels have greater than 150 ps skew between them. This requires that the oscilloscope be deskewed first. Swap out the channels that have more than 150 ps of skew until all channels being used are within 150 ps. It is important to deskew the word generator channels before testing. This will ensure that the outputs switch simultaneously.
- Terminate all inputs and outputs to ensure proper loading of the outputs and that the input levels are at the correct voltage.
- 4. Set V<sub>CC</sub> to 5.0V.
- Set the word generator to toggle all but one output at a frequency of 1 MHz. Greater frequencies will increase DUT heating and affect the results of the measurement.

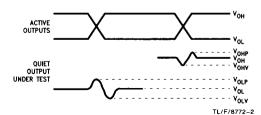


FIGURE 1. Quiet Output Noise Voltage Waveforms

Note A.  $V_{OHV}$  and  $V_{OHP}$  are measured with respect to  $V_{OH}$  reference.  $V_{OLV}$  and  $V_{OLP}$  are measured with respect to ground reference.

Note B. Input pulses have the following characteristics: f = 1 MHz, t<sub>f</sub> = 3 ns, t<sub>f</sub> = 3 ns, skew < 150 ps.

Set the word generator input levels at 0V LOW and 3V HIGH. Verify levels with a digital volt meter.

### VOLP/VOLV and VOHP/VOHV:

- Determine the quiet output pin that demonstrates the greatest noise levels. The worst case pin will usually be the furthest from the ground pin. Monitor the output voltages using a 50Ω coaxial cable plugged into a standard SMB type connector on the test fixture. Do not use an active FET probe.
- Verify that the GND reference recorded on the oscilloscope has not drifted to ensure the accuracy and repeatability of the measurements.

# **ALS Noise Characteristics (Continued)**

VII n and VIHO:

- Monitor one of the switching outputs using a  $50\Omega$  coaxial cable plugged into a standard SMB type connector on the test fixture. Do not use an active FET probe
- First increase the input LOW voltage level, V<sub>IL</sub>, until the output begins to oscillate. Oscillation is defined as noise on the output LOW level that exceeds V<sub>IL</sub> limits, or on output HIGH levels that exceed V<sub>IH</sub> limits. The input LOW voltage level at which oscillation occurs is defined as V<sub>II D</sub>.
- Next decrease the input HIGH voltage level on the word generator, V<sub>IH</sub> until the output begins to oscillate. Oscillation is defined as noise on the output LOW level that exceeds V<sub>IL</sub> limits, or on output HIGH levels that exceed V<sub>IH</sub> limits. The input HIGH voltage level at which oscillation occurs is defined as V<sub>IHD</sub>.
- Verify that the GND reference recorded on the oscilloscope has not drifted to ensure the accuracy and repeatability of the measurements.

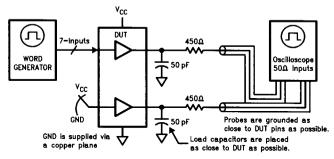
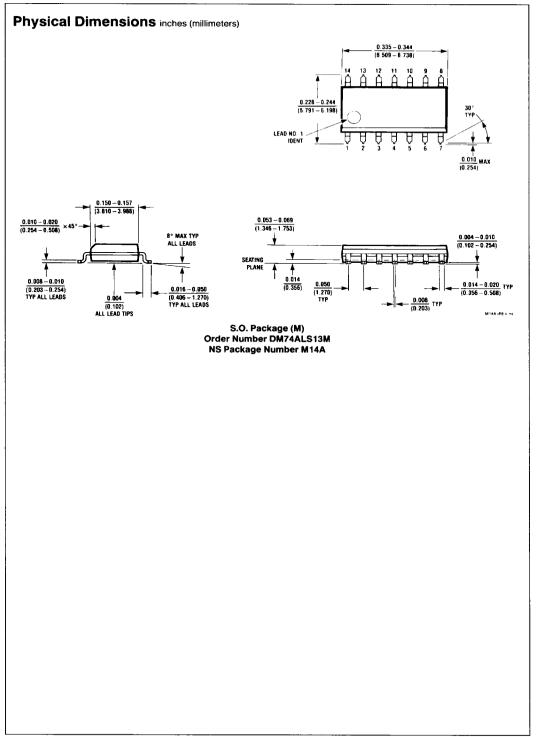
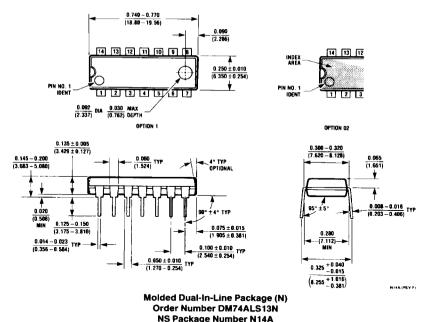


FIGURE 2. Simultaneous Switching Test Circuit

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